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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
HITOSHI KATO, ET AL. : EXAMINER: TO BE ASSIGNED  
SERIAL NO: 10/518,025 :  
FILED: DECEMBER 15, 2004 : GROUP ART UNIT: TO BE ASSIGNED  
FOR: CVD METHOD FOR FORMING :  
SILICON NITRIDE FILM ON TARGET  
SUBSTRATE

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Remarks/Arguments** begin on page 3 of this paper.